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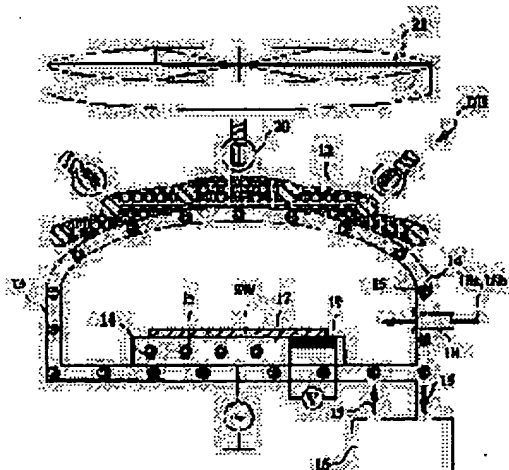
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## (54) METHOD AND DEVICE FOR MANUFACTURING SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE

## (57)Abstract:

**PROBLEM TO BE SOLVED:** To provide a technology that can reduce the manufacturing cost of a semiconductor integrated circuit device.

**SOLUTION:** In a method for manufacturing semiconductor integrated circuit device, a W film formed on a wafer SW is etched by heating the wafer SW to about 100-250° C by using all or part of infrared lamps 20, a temperature-adjusting liquid, a heating gas 18a, and a Peltier element 19. Then, a polycrystalline silicon film formed on the wafer SW is etched continuously by cooling the wafer SW to about -30 to 80° C by using all or part of the temperature-adjusting liquid 15, a cooling gas 18b, and the Peltier element 19.



## LEGAL STATUS

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